

ABSTRACT OF THE DISCLOSURE

A semiconductor photodetection device includes a semiconductor structure including an optical absorption
5 layer having a photo-incidence surface on a first side thereof, a dielectric reflecting layer formed on a second side of the semiconductor structure opposite to the first side, a contact electrode surrounding the dielectric reflecting layer and contacting with the semiconductor
10 structure, and a close contact electrode covering the dielectric reflecting layer and contacting with the contact electrode and the dielectric reflecting layer, wherein the close contact electrode adheres to the dielectric reflecting layer more strongly than to the contact electrode.